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STPS30M60C

Power Schottky rectifier

Features

- High current capability
- Avalanche rated
- Low forward voltage drop
- High frequency operation

Description

The STPS30M60C is a dual diode Schottky rectifier, suited for high frequency switch mode power supply.

Packaged in TO-220AB, I²PAK and D²PAK, this device is intended to be used in notebook, game station and desktop adapters, providing in these applications a good efficiency at both low and high load.

Table 1. Device summary						
Symbol	Value					
I _{F(AV)}	2 x 15 A					
V _{RRM}	60 V					
V _F (typ)	0.380 V					

150 °C

T_i (max)

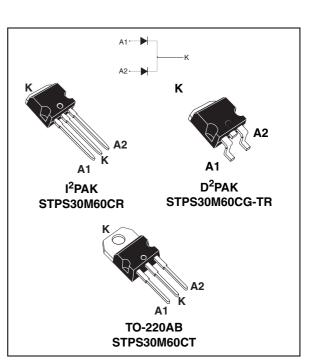
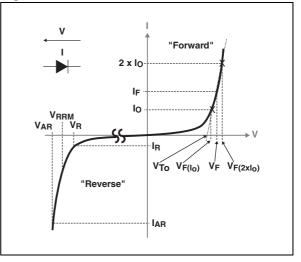


Figure 1. Electrical characteristics^(a)



 V_{ARM} and I_{ARM} must respect the reverse safe operating area defined in *Figure 12*. V_{AR} and I_{AR} are pulse measurements (t_p < 1 μs). V_R, I_R, V_{RRM} and V_F, are static characteristics

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Characteristics 1

Absolute ratings (limiting values, per diode, at T_{amb} = 25 °C unless Table 2. otherwise specified)

Symbol		Value	Unit			
V _{RRM}	Repetitive peak reverse volt	age			60	V
I _{F(RMS)}	Forward rms current				60	А
1	Average forward current, δ =	- 0 5	T _c = 135 °C	Per diode	15	А
I _{F(AV)}	Average forward current, o	T _c = 135 °C	Per device	30	A	
I _{FSM}	Surge non repetitive forward current $t_p = 10 \text{ ms sine-wave}$				400	А
P _{ARM} ⁽¹⁾	Repetitive peak avalanche	epetitive peak avalanche power $T_j = 25 \text{ °C}, t_p = 1 \mu\text{s}$			17600	W
V _{ARM} ⁽²⁾	Maximum repetitive peak avalanche voltage	t _p < 1 μs, T _j < 1	80	V		
V _{ARM} ⁽²⁾	Maximum single-pulse peak avalanche voltage	t _p < 1 μs, T _j < 1	80	V		
T _{stg}	Storage temperature range	-65 to +175	°C			
Тj	Maximum operating junction		150	°C		

1. For temperature or pulse time duration deratings, please refer to *Figure 4* and *5*. More details regarding the avalanche energy measurements and diode validation in the avalanche are provided in the application notes AN1768 and AN2025.

2. See Figure 12

 $\frac{dPtot}{dTj} < \frac{1}{Rth(j-a)}$ condition to avoid thermal runaway for a diode on its own heatsink 3.

Table 3. **Thermal parameters**

Symbol	Parameter	Value	Unit	
Б	per dio	de	1.3	°C/W
R _{th(j-c)} Junction to case	total		0.73	C/ W
R _{th(c)}	Coupling		0.15	°C/W

When the two diodes 1 and 2 are used simultaneously:

 ΔT_{i} (diode 1) = P(diode 1) x R_{th(i-c)}(Per diode) + P(diode 2) x R_{th(c)}



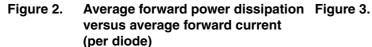
Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
I _B ⁽¹⁾	Reverse leakage current	T _j = 25 °C	V – V	-	20	80	μA
'R` ´	IR' / Reverse leakage current	T _j = 125 °C	$V_{R} = V_{RRM}$	-	15	50	mA
	Forward voltage drop	T _j = 25 °C		-	0.475	0.515	
V _F ⁽²⁾			F = 7.5 A	-	0.380	0.425	v
¥F`´	Forward voltage drop		L = 15 A	-	0.540	0.590	
	T _j = 1		F = 15 A	-	0.470	0.530	

 Table 4.
 Static electrical characteristics (per diode)

1. Pulse test: $t_p = 5 \text{ ms}, \delta < 2\%$

2. Pulse test: $t_p = 380 \ \mu s$, $\delta < 2\%$

To evaluate the conduction losses use the following equation: P = 0.385 x $I_{F(AV)}$ + 0.0097 x ${I_F}^2_{(RMS)}$



Average forward current versus ambient temperature (δ = 0.5, per diode)

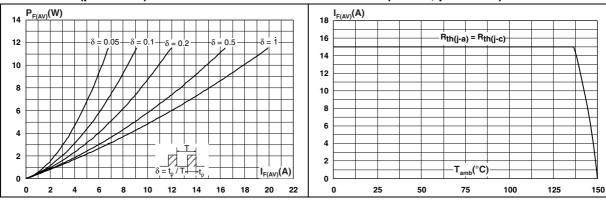


Figure 4. Normalized avalanche power derating versus pulse duration

Figure 5. Normalized avalanche power derating versus junction temperature

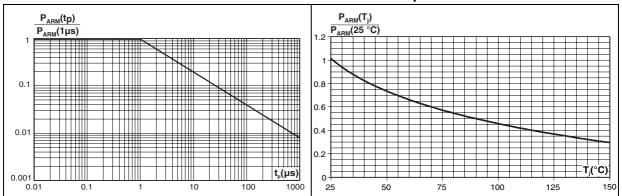
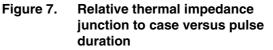
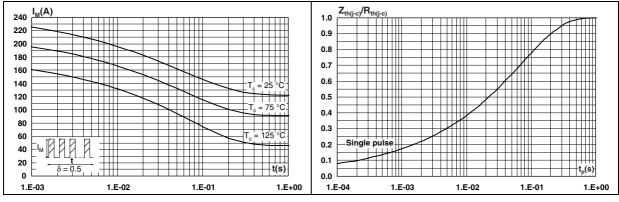
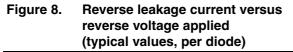
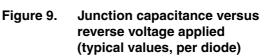


Figure 6. Non repetitive surge peak forward Figure 6. (maximum values, per diode)









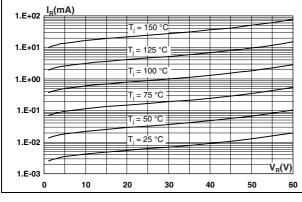


Figure 10. Forward voltage drop versus forward current (per diode)

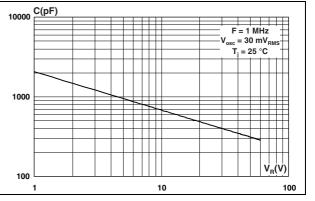
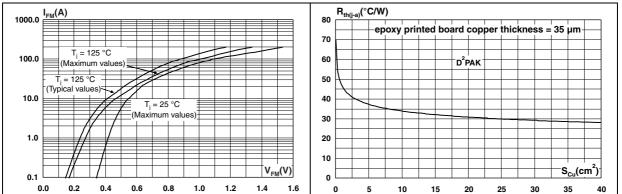


Figure 11. Thermal resistance junction to ambient versus copper surface under tab





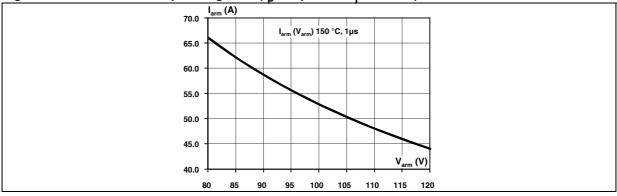


Figure 12. Reverse safe operating area (t_p < 1 μ s and T_i < 150 °C)



2 Package information

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.4 to 0.6 N·m

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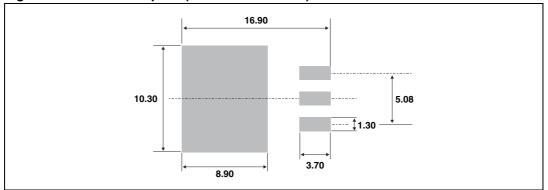
Table 5. TO-220AB dimensions

				Dimer	nsions								
									Ref.	Millin	neters	Inc	hes
			Min.	Max.	Min.	Max.							
		А	4.40	4.60	0.173	0.181							
		С	1.23	1.32	0.048	0.051							
H2 Dia	A	D	2.40	2.72	0.094	0.107							
		E	0.49	0.70	0.019	0.027							
	L7	F	0.61	0.88	0.024	0.034							
L6		F1	1.14	1.70	0.044	0.066							
		F2	1.14	1.70	0.044	0.066							
F2		G	4.95	5.15	0.194	0.202							
	D	G1	2.40	2.70	0.094	0.106							
L4		H2	10	10.40	0.393	0.409							
F→←		L2	16.4	Тур.	0.645	5 Тур.							
G1	M E	L4	13	14	0.511	0.551							
	⊫ E →	L5	2.65	2.95	0.104	0.116							
G		L6	15.25	15.75	0.600	0.620							
		L7	6.20	6.60	0.244	0.259							
		L9	3.50	3.93	0.137	0.154							
		М	2.6	Тур.	0.102	2 Тур.							
		Dia.	3.75	3.85	0.147	0.151							

			Dimensions				
		Ref.	Millim	neters	Inc	hes	
			Min.	Max.	Min.	Max.	
		А	4.40	4.60	0.173	0.181	
	← A →	A1	2.49	2.69	0.098	0.106	
	C2→→	A2	0.03	0.23	0.001	0.009	
		В	0.70	0.93	0.027	0.037	
L		B2	1.14	1.70	0.045	0.067	
		С	0.45	0.60	0.017	0.024	
↓ <u> </u>		C2	1.23	1.36	0.048	0.054	
$\rightarrow B^{B2}$		D	8.95	9.35	0.352	0.368	
G		Е	10.00	10.40	0.393	0.409	
		G	4.88	5.28	0.192	0.208	
		L	15.00	15.85	0.590	0.624	
	M↓ ★↓ V2	L2	1.27	1.40	0.050	0.055	
	* FLAT ZONE NO LESS THAN 2mm	L3	1.40	1.75	0.055	0.069	
	TER ZONE NO LESS THAN ZIIIII	М	2.40	3.20	0.094	0.126	
		R	0.40	typ.	0.016	6 typ.	
		V2	0°	8°	0°	8°	

Table 6.D²PAK dimensions

Figure 13. D²PAK footprint (dimensions in mm)



			Dimensions			
		Ref.	Millimeters		Inc	hes
			Min.	Max.	Min.	Max.
		А	4.40	4.60	0.173	0.181
		A1	2.40	2.72	0.094	0.107
		b	0.61	0.88	0.024	0.035
	D	b1	1.14	1.70	0.044	0.067
		с	0.49	0.70	0.019	0.028
	A1	c2	1.23	1.32	0.048	0.052
		D	8.95	9.35	0.352	0.368
		е	2.40	2.70	0.094	0.106
		e1	4.95	5.15	0.195	0.203
· · · · · · · · · · · · · · · · · · ·	→ C	E	10	10.40	0.394	0.409
←e1	' ← e1 →	L	13	14	0.512	0.551
		L1	3.50	3.93	0.138	0.155
		L2	1.27	1.40	0.050	0.055

Table 7.I²PAK dimensions



3 Ordering information

Table 8.Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STPS30M60CT	STPS30M60CT	TO-220AB	2.20 g	50	Tube
STPS30M60CR	STPS30M60CR	I ² PAK	1.49 g	50	Tube
STPS30M60CG-TR	STPS30M60CG	D ² PAK	1.48 g	1000	Tape and reel

4 Revision history

Date	Revision	Changes
02-Nov-2011	1	First issue.



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